

Supplemental Materials for “**Ab initio simulations of defect-based magnetism: The case of CoSi nanowires**”

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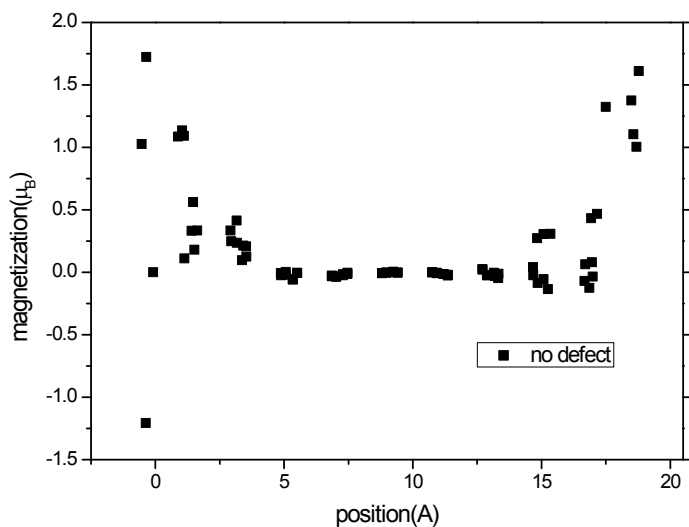


Figure S1. Distribution of simulated moment of Co atoms around SiO₂/CoSi (without ordered vacancies)/SiO₂ interface and the chosen three Co atoms with different distances to the interface based on LDA+U for single k-point and total drift force less than 0.17 eV/Å (<https://www.materialsproject.org/materials/mp-18748/GGA+U>, Co 3.32eV, the Ceder's Materialsproject home page)

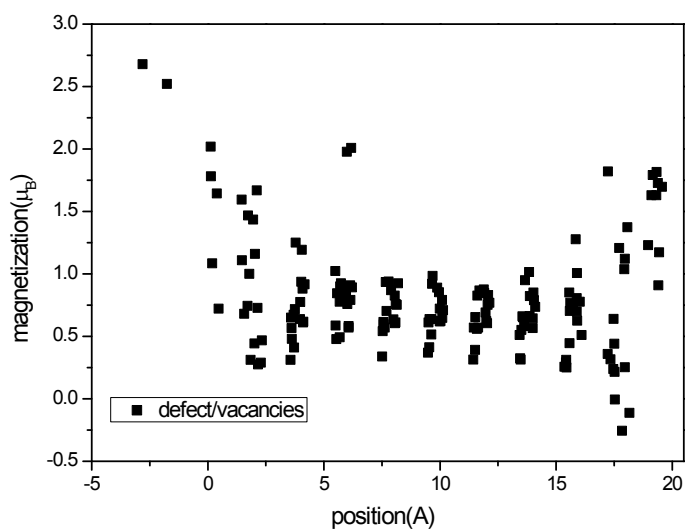
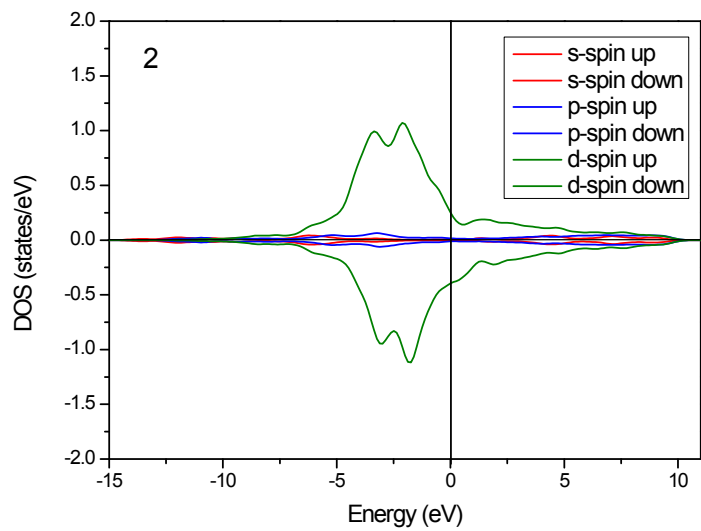
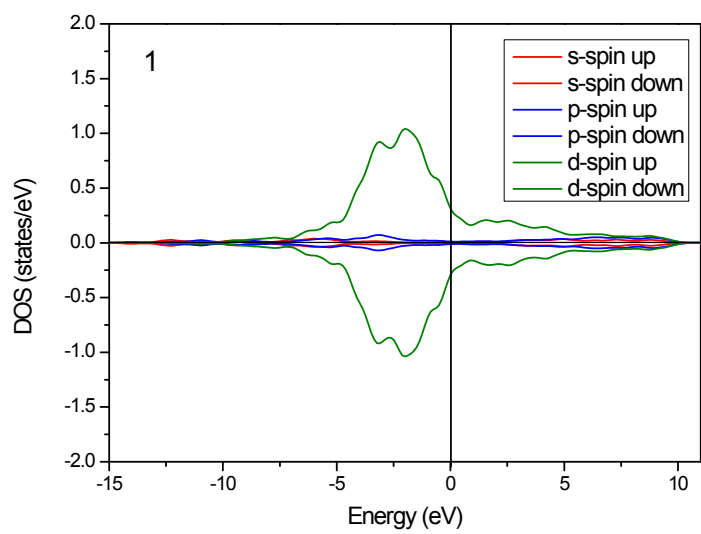


Figure S2. Distribution of simulated moment of Co atoms around SiO₂/CoSi (with ordered vacancies)/SiO₂ interface and the chosen three Co atoms with different distance to the interface based on LDA+U



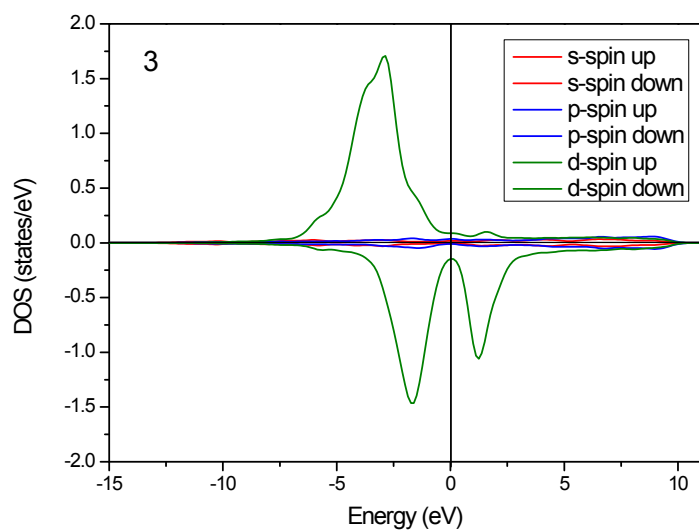
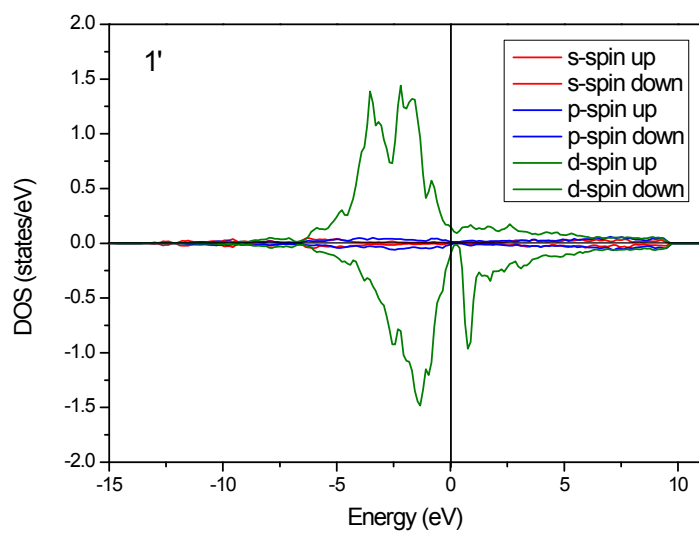


Figure S3. Corresponding DOS's of Fig.3 (LDA+U)



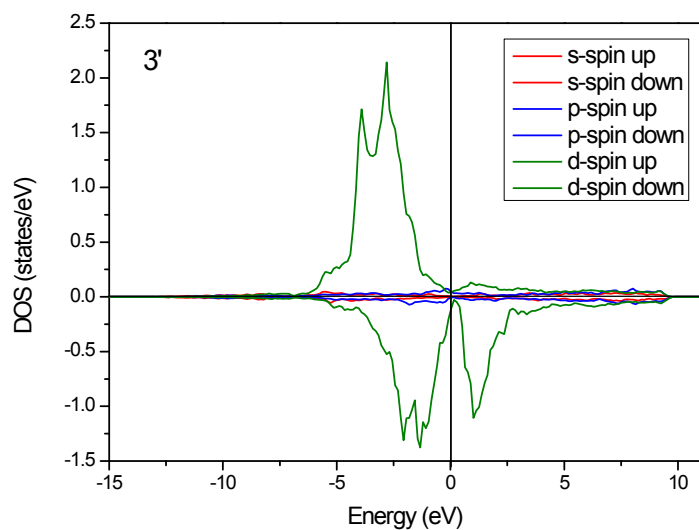
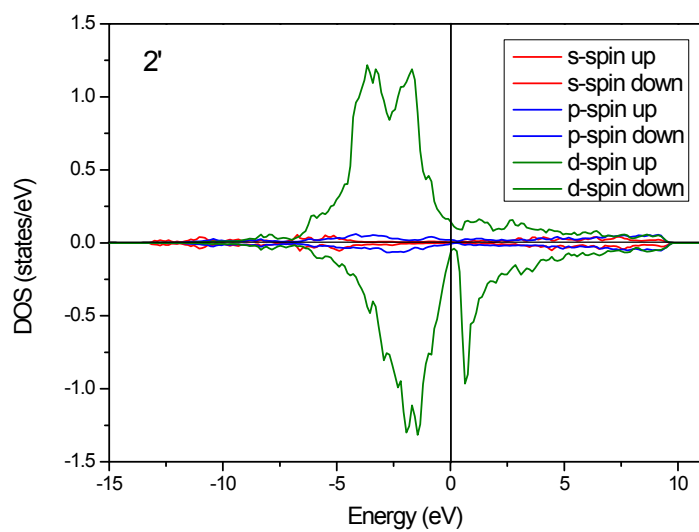


Figure S4. Corresponding DOS's of Fig. 4 (LDA+U), which become less symmetric due to existence of vacancies.

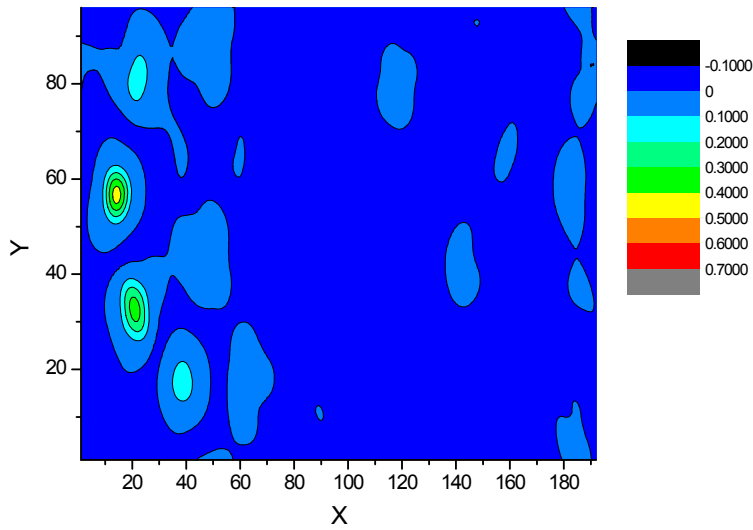


Figure S5. Contour of the electron density for spin-up minus spin-down at the 2' atom layer. (Y along [211] in the nanowire(long axis) and X along the inward direction in Fig. 4 in unit of Å)

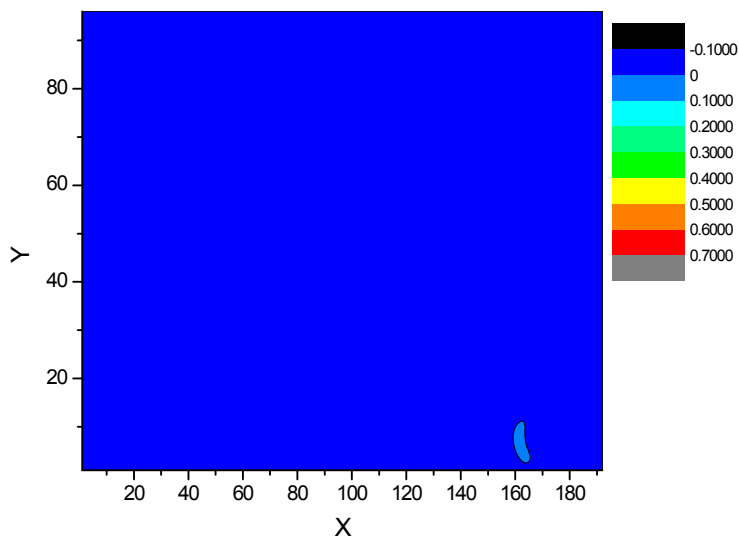


Figure S6. Contour of the electron density for spin-up minus spin-down at the 1' atom layer(Y along [211] in the nanowire(long axis) and X along the inward direction in Fig. 4 in unit of Å)